

S/N 09/135,413

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Leonard Forbes et al.

Serial No.: 09/135,413

Filed: August 14, 1998

Title: METHOD FOR OPERATING A DEAPROM HAVING AN AMORPHOUS  
SILICON CARBIDE GATE INSULATOR



PATENT

Examiner: Viet Q. Nguyen

Group Art Unit: 2818

Docket: 303.354US2

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10/22/99

**AMENDMENT AND RESPONSE**

Assistant Commissioner for Patents  
Washington, D.C. 20231

10/18/99

In response to the Office Action mailed July 9, 1999, please amend the above identified patent application as follows:

**IN THE CLAIMS**

**RECEIVED**

Please amend the claims as follows:

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15. (Amended) A method for operating a floating gate transistor comprising:  
programming the floating gate transistor by inducing charge to migrate from a channel in a substrate through [a] an amorphous silicon carbide (a-SiC) gate insulator to a floating gate electrode in the floating gate transistor; and

erasing the floating gate transistor by inducing charge to migrate from the floating gate electrode through the amorphous silicon carbide (a-SiC) gate insulator to the channel.

16. (Amended) The method of claim 15 wherein:

programming comprises programming the floating gate transistor by inducing hot electron injection from a channel in a substrate through [an] the amorphous silicon carbide (a-SiC) gate insulator to a polysilicon floating gate electrode in the floating gate transistor; and

erasing comprises erasing the floating gate transistor by inducing charge to migrate from the polysilicon floating gate electrode through the amorphous silicon carbide (a-SiC) gate insulator to the channel through Fowler-Nordheim tunneling.

17. (Amended) A method for operating a floating gate transistor connected to a control line and a data line, the method comprising:

programming the floating gate transistor by providing a control voltage on the control

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